

INFORMATION DISCLOSURE
CITATION

ATTY. DOCKET NO.

925-178

APPLICANT

NAKAMURA et al

FILING DATE

May 1, 2000

SERIAL NO.

09/463,643

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2815

(Use several sheets if necessary)



U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	5,838,029	11/1998	Shakuda			
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X 03-252175	11/1991	Japan			ABS
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X	Akasaki et al Shortest wavelength semiconductor laser diode, Electronics Letters Vol. 32, No. 12, pp. 1105-1106, June 6, 1996
X	Akasaki et al Stimulated Emission by Current Injection from an AlGaIn/GaN/GaInN Quantum Well Device, Jpn. J. Appl. Phys. Vol. 34, pp L1517-L1519, 1995
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*Examiner

Date Considered

7/11/03

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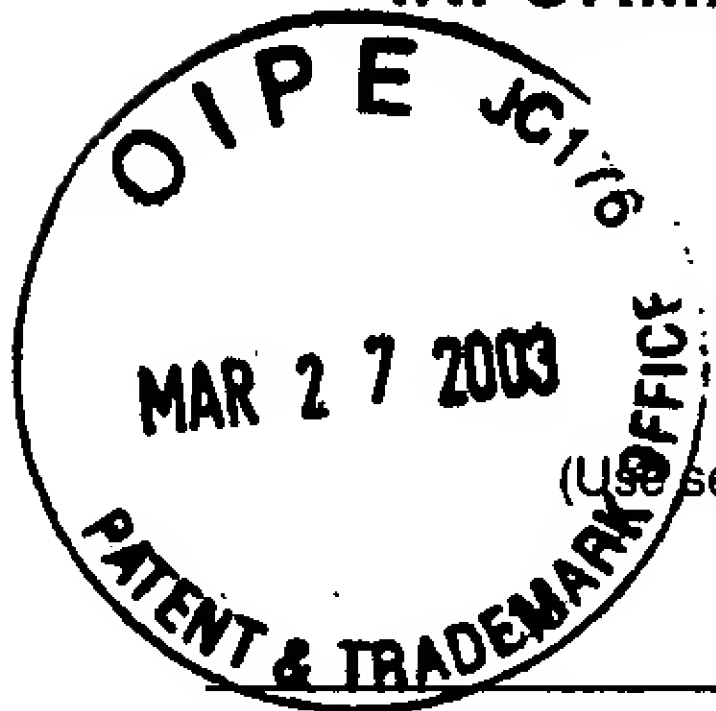
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